2.5V Drive Nch+Nch MOS FET

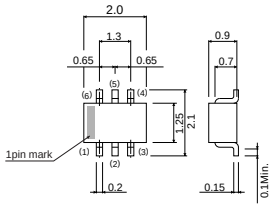
UM6K1N

●Structure
Silicon N-channel MOS FET

●Features
1) Two 2SK3018 transistors in a single UMT package.
2) The MOS FET elements are independent, eliminating mutual interference.
3) Mounting cost and area can be cut in half.
4) Low On-resistance.
5) Low voltage drive (2.5V drive) makes this device ideal for portable equipment.

●External dimensions (Unit : mm)

UMT6



Each lead has same dimensions

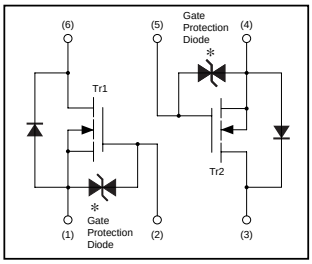
Abbreviated symbol : K1

●Applications
Interfacing, switching (30V, 100mA)

●Packaging specifications

Type	Package	Taping
	Code	TN
	Basic ordering unit (pieces)	3000
UM6K1N		○

●Inner circuit



(1) Tr1 Source
(2) Tr1 Gate
(3) Tr2 Drain
(4) Tr2 Source
(5) Tr2 Gate
(6) Tr1 Drain

✻ A protection diode has been built in between the gate and the source to protect against static electricity when the product is in use. Use the protection circuit when rated voltages are exceeded.

●Absolute maximum ratings (Ta=25°C)
<It is the same ratings for Tr1 and Tr2.>

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±100	mA
	Pulsed	I_{DP} *1	±400	mA
Total power dissipation		P_D *2	150	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	–55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%
*2 With each pin mounted on the recommended lands.

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a) *	833	°C / W / TOTAL
		1042	°C / W / ELEMENT

* With each pin mounted on the recommended lands.

●**Electrical characteristics** (Ta=25°C)

<It is the same characteristics for Tr1 and Tr2.>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±1	μA	V_{GS}=±20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	30	–	–	V	I_D= 10μA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	1.0	μA	V_{DS}= 30V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	0.8	–	1.5	V	V_{DS}= 3V, I_D= 100μA
Static drain-source on-state resistance	$R_{DS\ (on)}$	–	5	8	Ω	I_D= 10mA, V_{GS}= 4V
		–	7	13	Ω	I_D= 1mA, V_{GS}= 2.5V
Forward transfer admittance	$\|Y_{fs}\|$	20	–	–	mS	I_D= 10mA, V_{DS}= 3V
Input capacitance	C_{iss}	–	13	–	pF	V_{DS}= 5V
Output capacitance	C_{oss}	–	9	–	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	–	4	–	pF	f=1MHz
Turn-on delay time	$t_{d\ (on)}$	–	15	–	ns	V_{DD} ≒ 5V
Rise time	t_r	–	35	–	ns	I_D= 10mA
Turn-off delay time	$t_{d\ (off)}$	–	80	–	ns	V_{GS}= 5V
Fall time	t_f	–	80	–	ns	R_L=500Ω
						R_G=10Ω

●**Electrical characteristic curves**

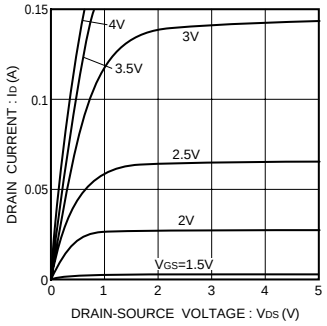


Fig.1 Typical Output Characteristics

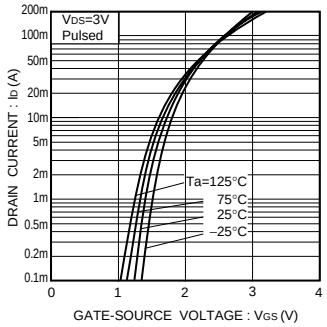


Fig.2 Typical Transfer Characteristics

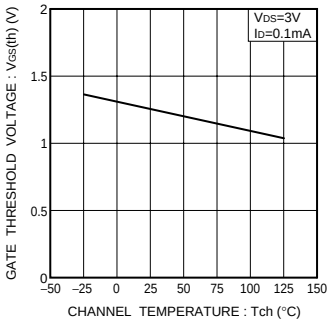


Fig.3 Gate Threshold Voltage vs. Channel Temperature

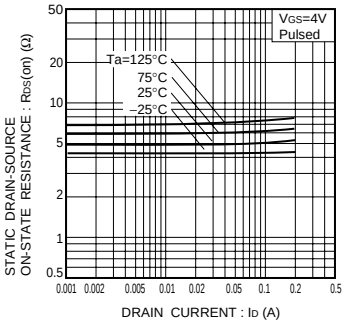


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (Ⅰ)

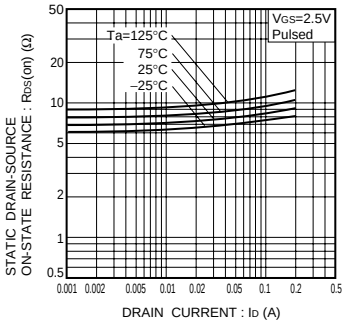


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current (Ⅱ)

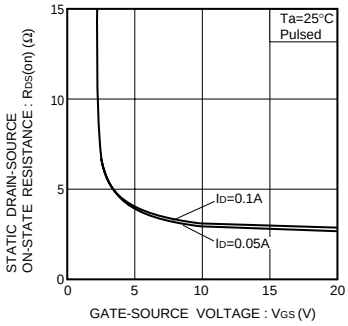


Fig.6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

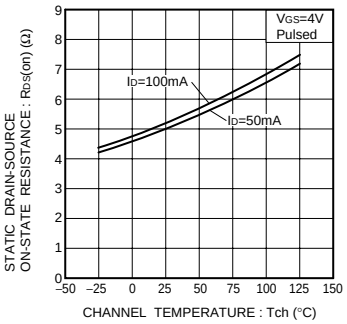


Fig.7 Static Drain-Source On-State Resistance vs. Channel Temperature

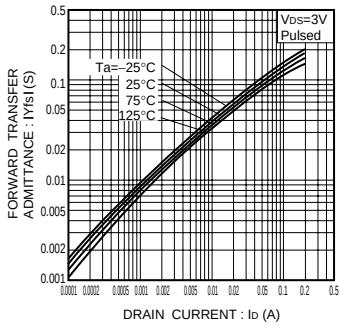


Fig.8 Forward Transfer Admittance vs. Drain Current

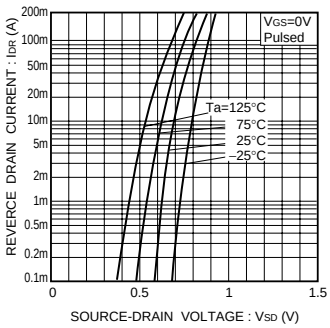


Fig.9 Reverse Drain Current vs. Source-Drain Voltage (Ⅰ)

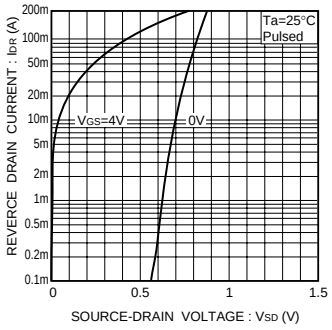


Fig.10 Reverse Drain Current vs. Source-Drain Voltage (Ⅱ)

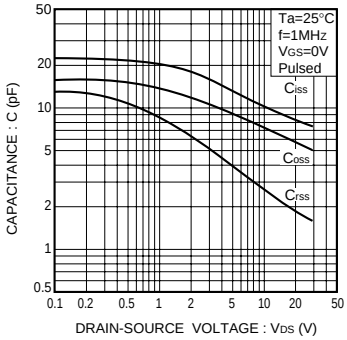


Fig.11 Typical Capacitance vs. Drain-Source Voltage

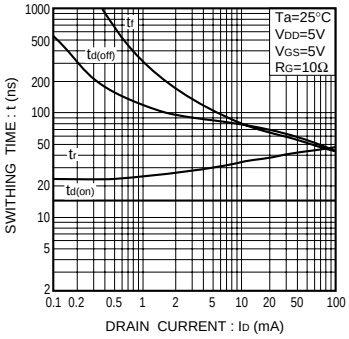


Fig.12 Switching Characteristics

●Switching characteristics measurement circuit

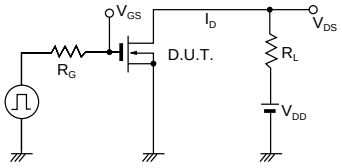


Fig.13 Switching Time Test Circuit

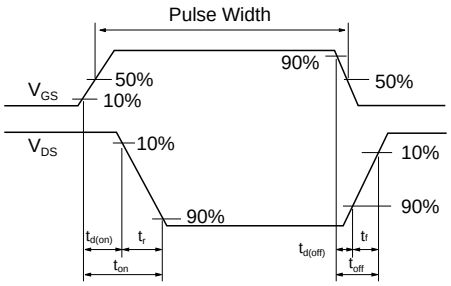


Fig.14 Switching Time Waveforms

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